P 沟道增强型场效应晶体管

P-CHANNEL MOSFET

FHU9540C/FHD9540C

主要参数 MAIN CHARACTERISTICS

ID	-35 A
VDSS	-100 V
Rdson-typ（ @Vgs=10V）	32mΩ
Rdson-typ（ @Vgs=4.5V）	36mΩ
Qg-typ	66nC

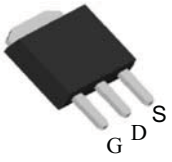
产品特性 FEATURES

低栅极电荷	Low gate charge
低 Crss (典型值 190pF)	Low Crss (typical 190pF)
开关速度快	Fast switching
100%经过雪崩测试	100% avalanche tested
高抗 dv/dt 能力	Improved dv/dt capability
RoHS 产品	RoHS product

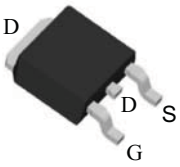
用途 APPLICATIONS

负载开关	Load switch

封装形式 Package

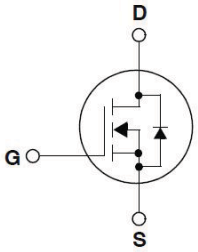


TO-251
FHU series



TO-252
FHD series

等效电路 Equivalent Circuit



绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项目 **Parameter**	符号 **Symbol**	数值 **Value**		单位 **Unit**
		FHU9540C	**FHD9540C**	
最高漏极－源极直流电压 Drain-Source Voltage	V_{DS}	-100		V
连续漏极电流* Drain Current -continuous *	I_D（Tc=25℃）	-35		A
	I_D（Tc=100℃）	-25		A
最大脉冲漏极电流（注 1） Drain Current – pulse（note 1）	I_{DM}	-140		A
最高栅源电压 Gate-Source Voltage	V_{GS}	±20		V
单脉冲雪崩能量（注 2） Single Pulsed Avalanche Energy（note 2）	E_{AS}	480		mJ
雪崩电流（注 1） Avalanche Current（note 1）	I_{AR}	17		A
重复雪崩能量（注 1） Repetitive Avalanche Current（note 1）	E_{AR}	16		mJ
二极管反向恢复最大电压变化速率（注 3） Peak Diode Recovery dv/dt（note 3）	dv/dt	5.0		V/ns
耗散功率 Power Dissipation	P_D （TC=25℃）	105		W
	-Derate above 25℃	0.71		W/℃
最高结温及存储温度 Operating and Storage Temperature Range	T_J，T_{STG}	-55～+150		℃
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T_L	300		℃

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature

电特性 ELECTRICAL CHARACTERISTICS

项目 **Parameter**	符号 **Symbol**	测试条件 **Tests conditions**	最小 **Min**	典型 **Typ**	最大 **Max**	单位 **Units**
关态特性 **Off –Characteristics**						
漏－源击穿电压 Drain-Source Voltage	BV_{DSS}	I_D=-250μA, V_{GS}=0V	-100	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta TJ$	I_D=-250μA, referenced to 25℃	-	-0.1	-	V/℃
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-100V,V_{GS}=0V, T_C=25℃	-	-	-1	μA
		V_{DS}=-80V, T_C=125℃	-	-	-10	μA
栅极体漏电流 Gate-body leakage current	I_{GSS}（F/R）	V_{DS}=0V, V_{GS} =±20V	-	-	±100	nA
通态特性 **On-Characteristics**						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = VGS , I_D=-250μA	-1.3	-1.95	-2.5	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS} =-10V , I_D=-15A	-	32	38	mΩ
		V_{GS} =-4.5V , I_D=-10A	-	36	45	
正向跨导 Forward Transconductance	gfs	V_{DS} = -5V, I_D=-12A（note 4）	-	28	-	S
动态特性 **Dynamic Characteristics**						
栅电阻 Gate Resistance	Rg	f=1.0MHz, V_{DS} OPEN	-	1.5	-	Ω
输入电容 Input capacitance	Ciss	V_{DS}=-25V, V_{GS} =0V, f=1.0MHz	-	3100	-	pF
输出电容 Output capacitance	Coss		-	360	-	
反向传输电容 Reverse transfer capacitance	Crss		-	190	-	
开关特性 **Switching Characteristics**						
延迟时间 Turn-On delay time	td(on)	V_{DS}=-50V, I_D=-35A, R_G=4.7Ω V_{GS} =-10V （note 4，5）	-	15	-	ns
上升时间 Turn-On rise time	tr		-	17	-	ns
延迟时间 Turn-Off delay time	td(off)		-	31	-	ns
下降时间 Turn-Off Fall time	tf		-	53	-	ns
栅极电荷总量 Total Gate Charge	Qg	V_{DS} =-80V , I_D=-35A , V_{GS} =-10V （note 4，5）	-	66	-	nC
栅－源电荷 Gate-Source charge	Qgs		-	17	-	nC
栅－漏电荷 Gate-Drain charge	Qgd		-	23	-	nC
漏－源二极管特性及最大额定值 **Drain-Source Diode Characteristics and Maximum Ratings**						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	I_S		-	-	-35	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}		-	-	-140	A
正向压降 Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-35A	-	-0.82	-1.3	V
反向恢复时间 Reverse recovery time	trr	V_{GS}=0V, I_S=-35A ,dI_F/dt=100A/μs (note 4)	-	52	-	ns
反向恢复电荷 Reverse recovery charge	Qrr		-	96	-	nC

热特性 THERMAL CHARACTERISTIC

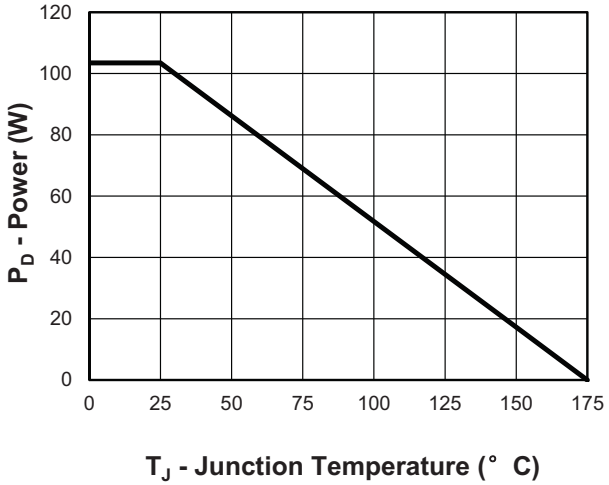
项目 Parameter	符号 Symbol	最大值 Max	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	Rth(j-c)	1.45	℃/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	Rth(j-A)	110	℃/W

注释：
1：脉冲宽度由最高结温限制
2：L=1mH, I_{AS}=-17A, V_{DD}=-48V, R_G=25 Ω,起始结温 T_J=25℃
3：I_{SD} ≤25A,di/dt ≤300A/μs,V_{DD}≤BV_{DSS},起始结温 T_J=25℃
4：脉冲测试：脉冲宽度 ≤300μs,占空比≤2%
5：基本与工作温度无关

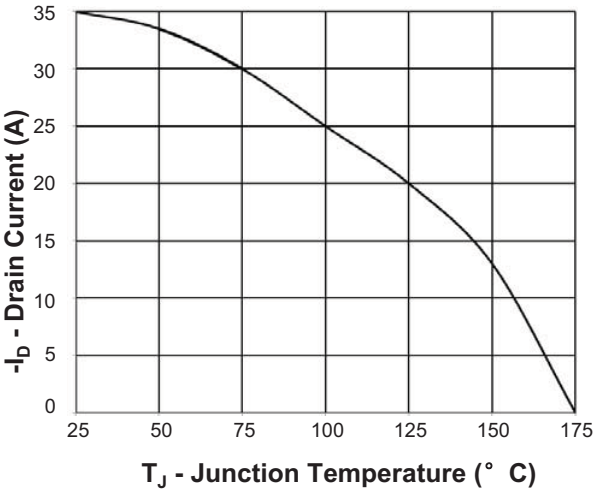
Notes:
1：Pulse width limited by maximum junction temperature
2：L=1mH, I_{AS}=-17A, V_{DD}=-48V, R_G=25 Ω,Starting T_J=25℃
3：I_{SD} ≤25A,di/dt ≤300A/μs,V_{DD}≤BV_{DSS}, Starting T_J=25℃
4：Pulse Test：Pulse Width ≤300μs,Duty Cycle≤2%
5：Essentially independent of operating temperatur

Typical Characteristics

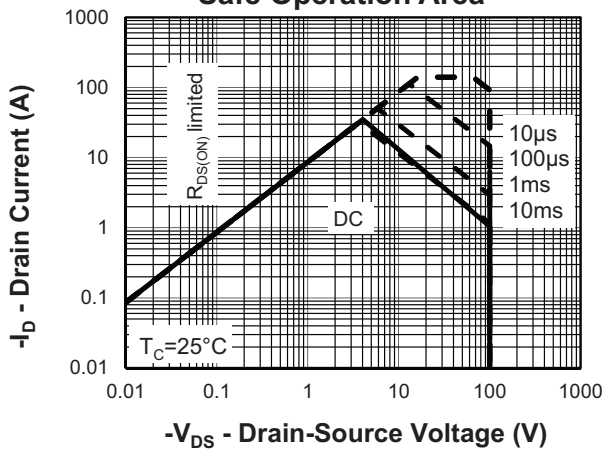
Power Dissipation



Drain Current



Safe Operation Area



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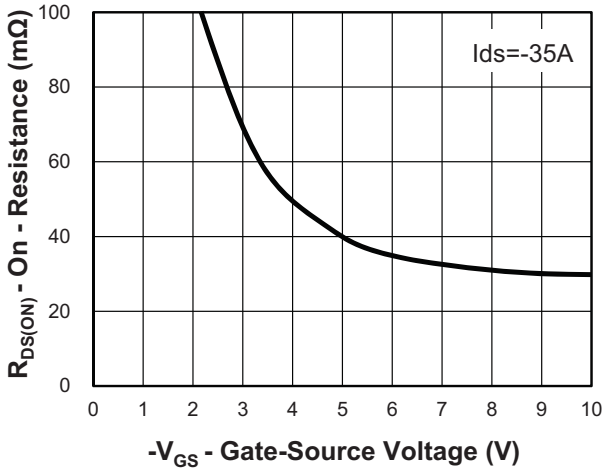
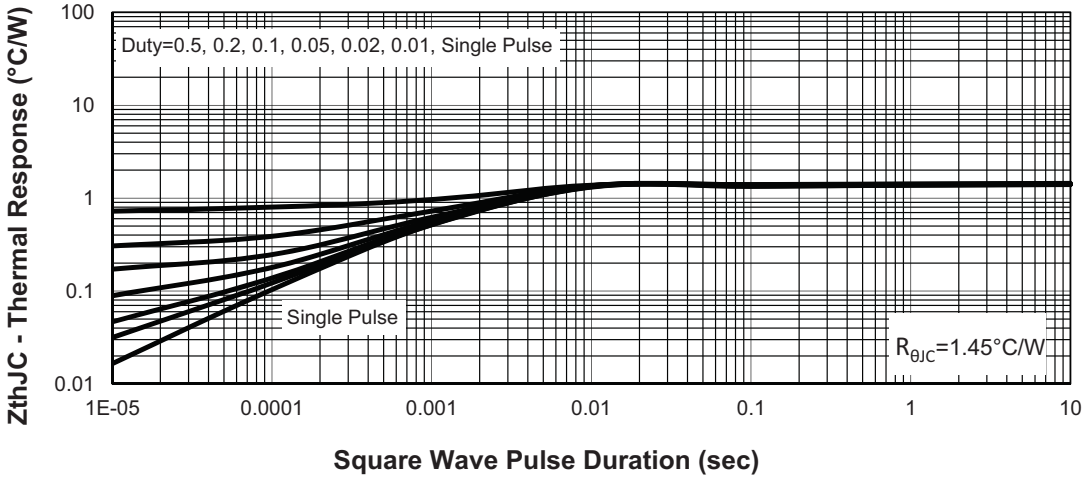
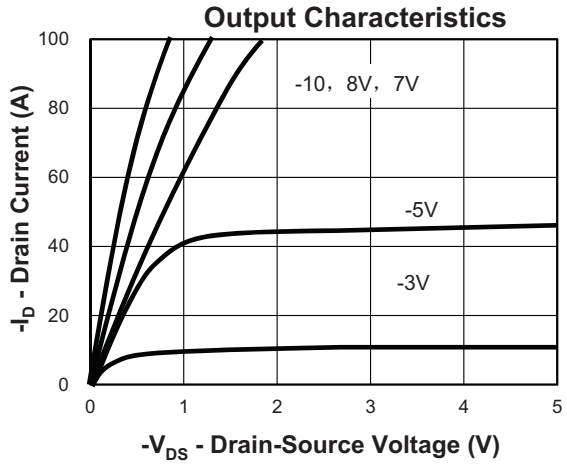
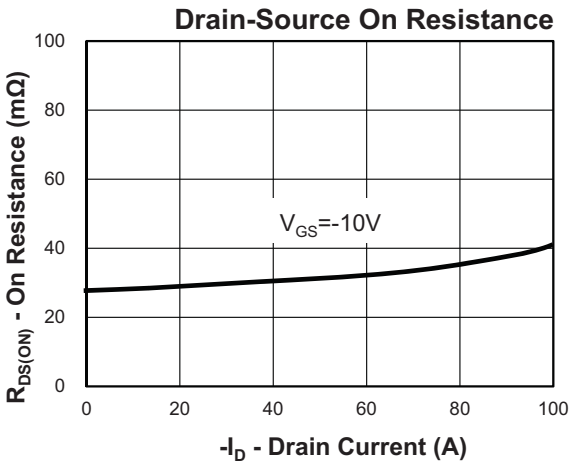


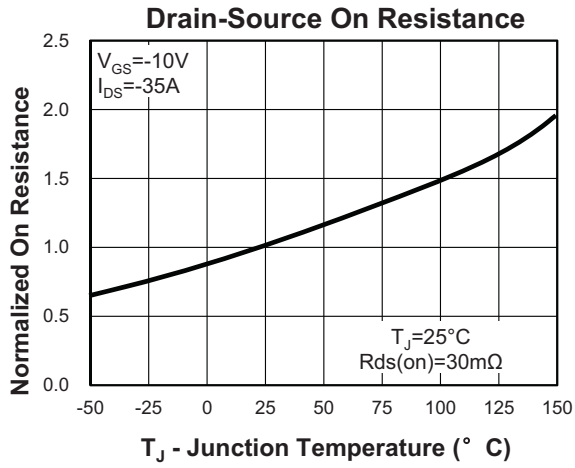
Thermal Transient Impedance

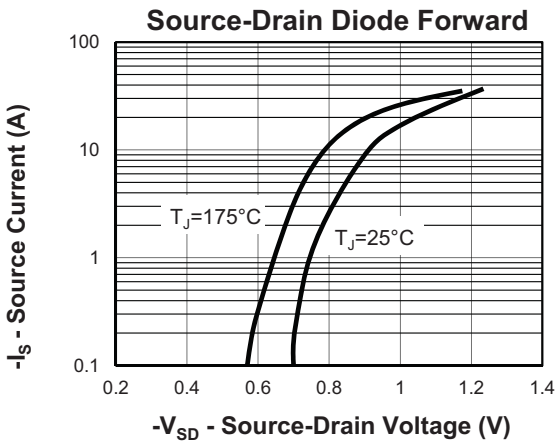


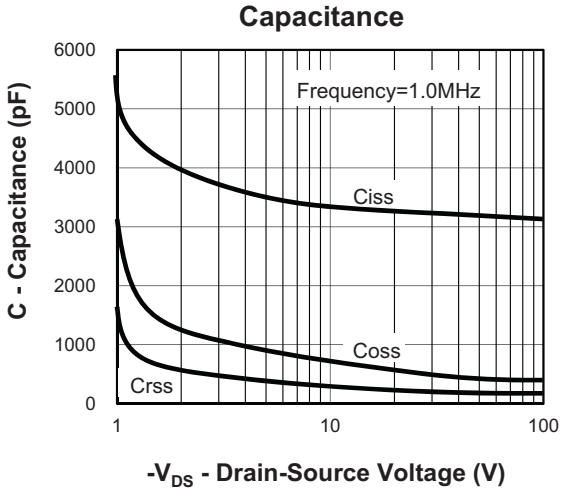
Typical Characteristics

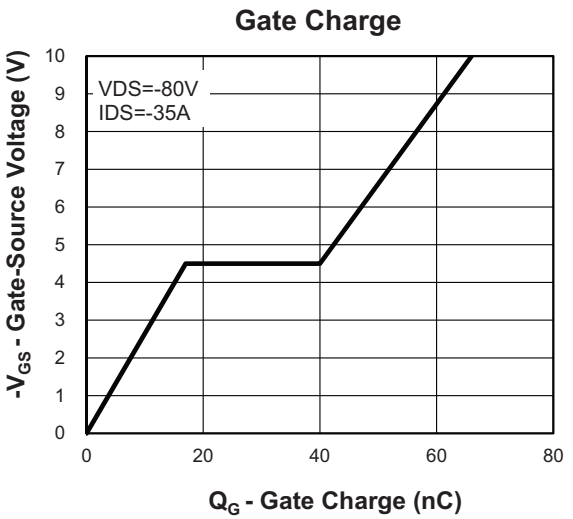


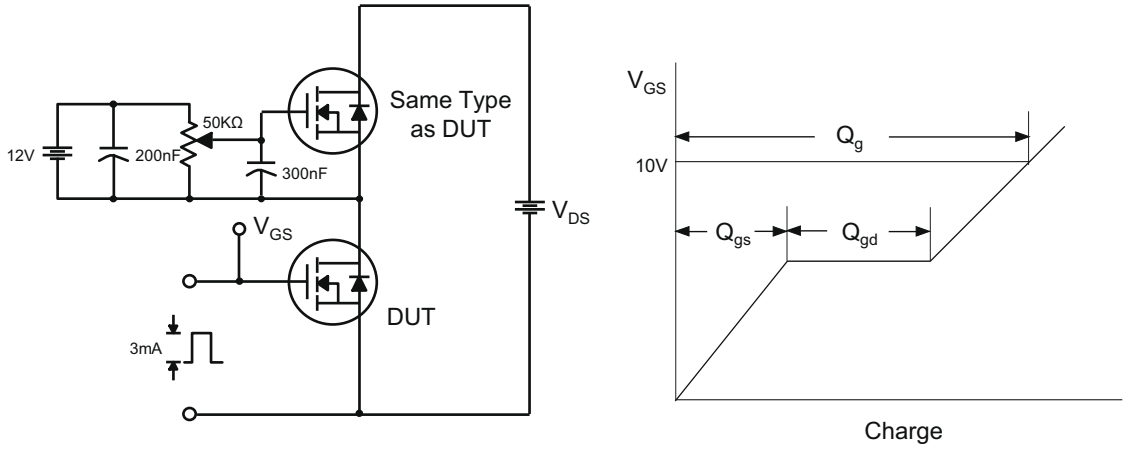




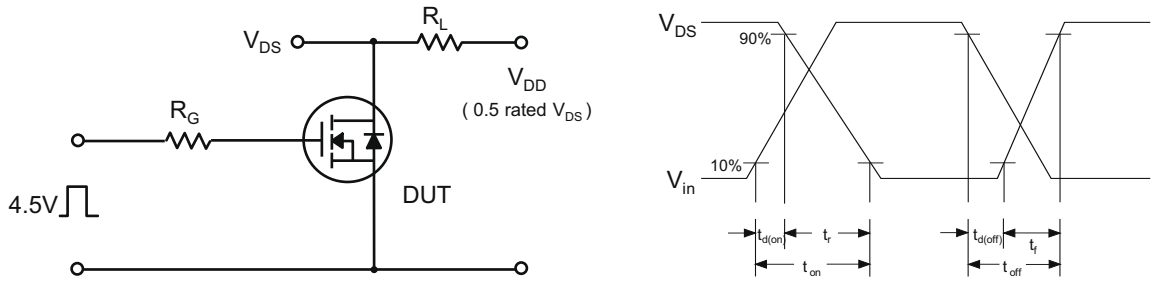




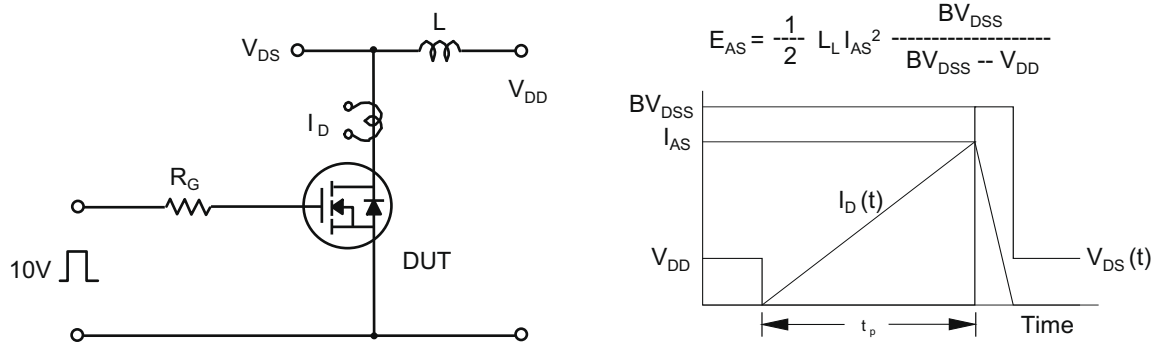




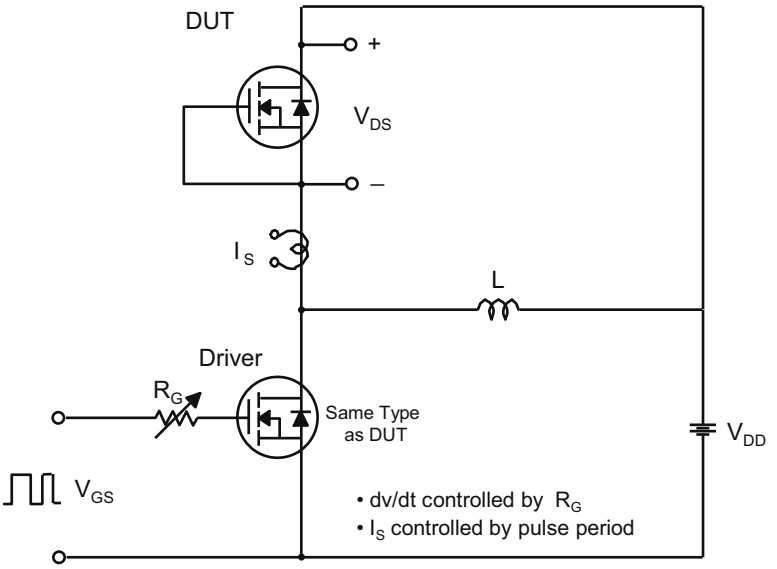
Gate Charge Test Circuit & Waveform

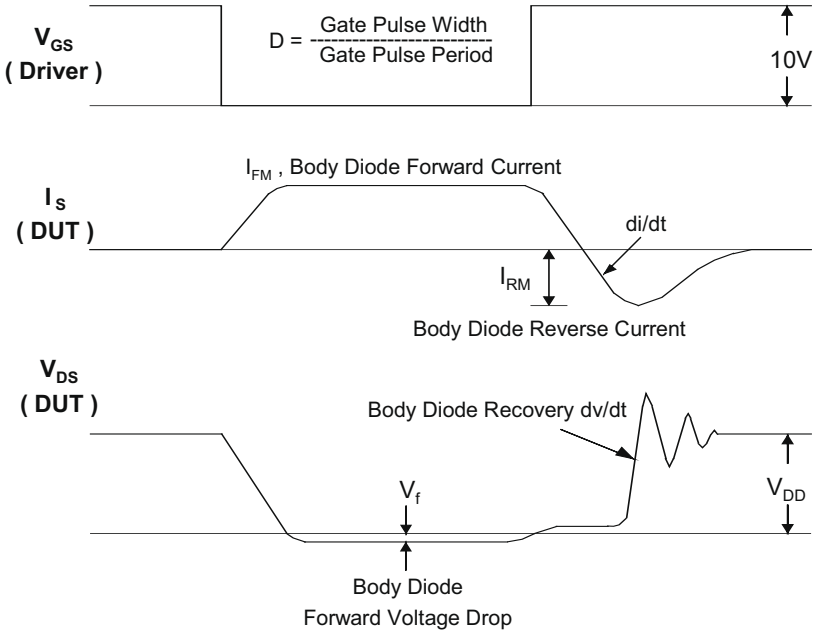


Resistive Switching Test Circuit & Waveforms



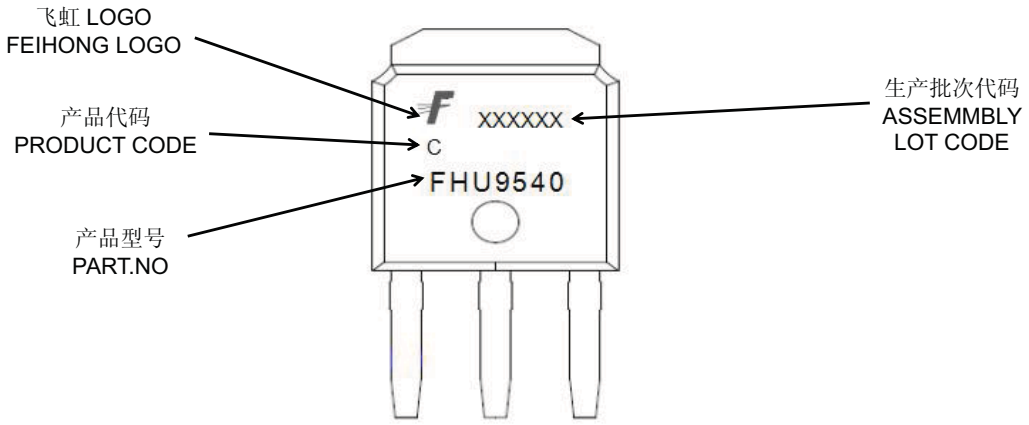
Unclamped Inductive Switching Test Circuit & Waveforms





Peak Diode Recovery dv/dt Test Circuit & Waveforms

印记 Marking:


飞虹 LOGO
FEIHONG LOGO
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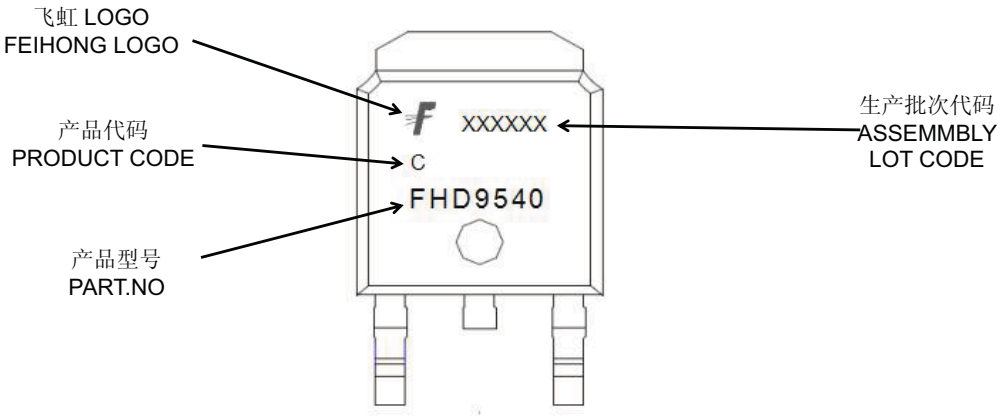
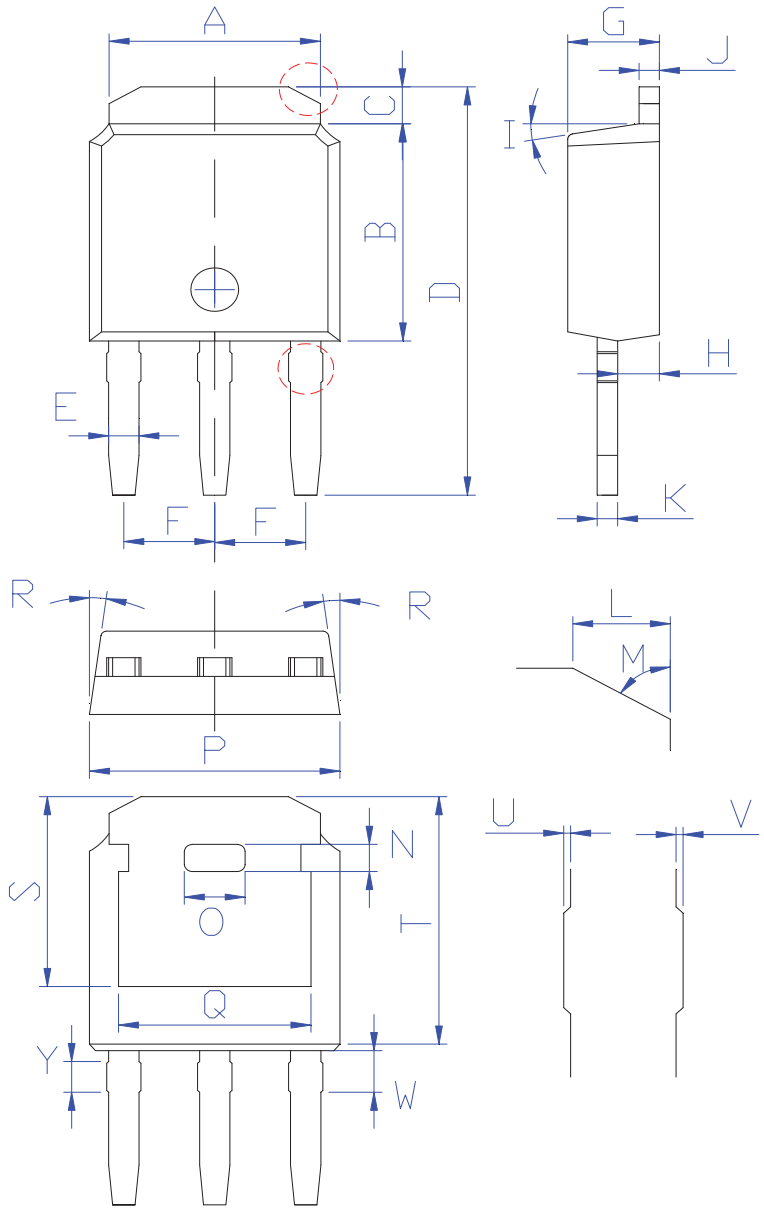
产品型号
PART.NO
XXXXXX
C
FHU9540
生产批次代码
ASSEMMBLY
LOT CODE


飞虹 LOGO
FEIHONG LOGO
产品代码
PRODUCT CODE
产品型号
PART.NO
XXXXXX
C
FHD9540
生产批次代码
ASSEMMBLY
LOT CODE

外形尺寸：

Package Dimension：

TO-251



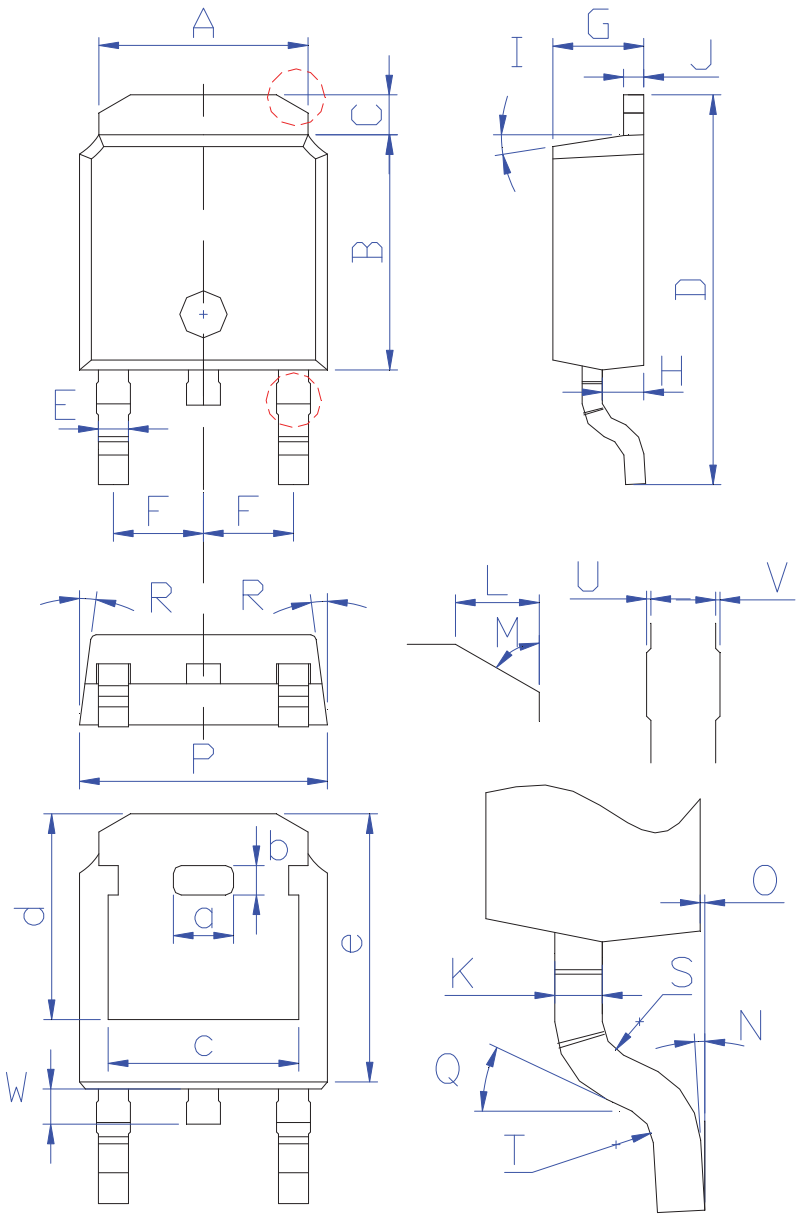
DIM	MILLIMETERS
A	5.34±0.30
B	6.00±0.30
C	1.05±0.30
D	11.31±0.30
E	0.76±0.15
F	2.28±0.15
G	2.30±0.30
H	1.06±0.30
I	(4-10)°
J	0.51±0.15
K	0.52±0.15
L	0.80±0.30
M	60°
N	0.75±0.30
O	1.80±0.30
P	6.60±0.30
Q	4.85±0.30
R	(4-8.5)°
S	5.30±0.30
T	6.90±0.30
U	0.05±0.05
V	0.05±0.05
W	1.15±0.25
Y	0.85±0.25

（Unit：mm）

外形尺寸：

Package Dimension：

TO-252



DIM	MILLIMETERS
A	5.34±0.30
B	6.00±0.30
C	1.05±0.30
D	9.95±0.30
E	0.76±0.15
F	2.28±0.15
G	2.30±0.30
H	1.06±0.30
I	(4-10)°
J	0.51±0.15
K	0.52±0.15
L	0.80±0.30
M	60°
N	(0-10)°
O	0.05±0.05
P	6.60±0.30
Q	25°
R	(4-8.5)°
S	R0.40
T	R0.40
U	0.05±0.05
V	0.05±0.05
W	0.90±0.30
a	1.80±0.30
b	0.75±0.30
c	4.85±0.30
d	5.30±0.30
e	6.90±0.30

(Units：mm)